

## **I. AMENDMENTS TO THE CLAIMS**

Claims 1 to 11. (Withdrawn and Canceled)

Claim 12. (Previously Presented) Dielectric films obtained from a PTFE-based formulation comprising:

- 1) a PTFE latex made of particles whose diameter is in the range of 5 nm to 100 nm, comprising an anionic fluorinated surfactant in an amount in the range of 2% to 25% by weight, based on PTFE;
- 2) a non-ionic fluorinated surfactant added to the PTFE latex in an amount in the range of 18% to 60% by weight, based on the PTFE, wherein  
the dielectric films are obtained from the formulation by depositing the formulation onto a substrate, then sintering the film obtained at a temperature above the PTFE melting point, and then air-cooling.

Claim 13. (Previously Presented) Dielectric films according to claim 12, wherein the deposition is carried out by spin coating at a spinning rate in the range of 3,000 rpm to 10,000 rpm for a time comprised between 30 seconds and 5 minutes and in which the sintering temperature is higher than 320°C.

Claim 14. (Previously Presented) Dielectric films according to claim 12 having a thickness lower than 200 nm, a dielectric constant lower than 2.2, a dielectric strength higher than 4 MV/cm and a weight loss at 425°C in the range of 0.0008%/min to 0.02%/min.

Claim 15. (Previously Presented) A method for the insulation of conductors in integrated circuits comprising utilizing dielectric films according to claim 12.